

Radiation Hardened Dual 3-Input Majority Voter

with cold sparing

1 GENERAL DESCRIPTION

The **AP54RHC301** is a radiation-hardened by design **dual 3-Input Majority Voter** that is ideally suited for space, medical imaging and other applications demanding radiation tolerance and high reliability. It is fabricated in a 180 nm CMOS process utilizing proprietary radiation-hardening techniques, delivering high resiliency to single-event effects (SEE) and to a total ionizing dose (TID) up to 30 krad (Si).

This device is a member of the Apogee Semiconductor AP54RHC logic family operating across a voltage supply range of **1.65 V to 5.5 V**.

The AP54RHC301 is an unique discrete majority voter logic function that offers two instances of a triple-input voter gate, with individual error outputs. In addition, a dedicated "error detected" indication is available, in addition to an external error input signal.

Zero-power penalty[™] cold-sparing is supported, along with Class 2 ESD protection on all inputs and outputs. A proprietary output stage and robust power-on reset (POR) circuit allow the AP54RHC301 to be cold-spared in any redundant configuration with no static power loss on any pad of the device. The redundant output stage also features a high drive capability with low static power loss.

The AP54RHC301 also features a triple-redundant design throughout its entire circuitry, which allows it to be immune to single-event transients (SET) without requiring additional redundant devices.

Ordering information may be found in Table 9 on Page 12.

1.1 FEATURES

- 1.65 VDC to 5.5 VDC operation
- Inputs tolerant up to 5.5 VDC at any V_{CC}
- Provides logic-level down translation to V_{CC}
- Extended operating temperature range (-55 °C to +125 °C)

- Proprietary **cold-sparing capability** with **zero** static power penalty
- Built-in triple redundancy for enhanced reliability

Internal power-on reset (POR) circuitry ensures

- reliable power up and power down responses during hot plug and cold sparing operations
- Class 2 ESD protection (4000 V HBM, 500 V CDM)
- TID resilience of 30 krad (Si)
- SEL resilient up to LET of 80 MeV-cm²/mg

1.2 LOGIC DIAGRAM

The AP54RHC301 logic function is shown below:

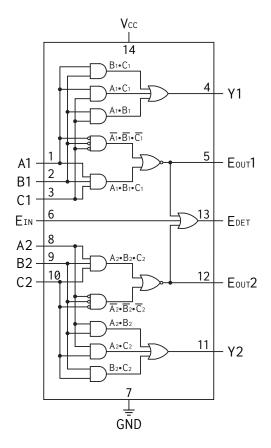


Figure 1: AP54RHC301 logic diagram

AP54RHC301 DATASHEET



CONTENTS

	•	1 1 1
Acro	onyms and Abbreviations	2
		3 3
Pin	Configuration	3
5.1 5.2 5.3	Absolute Maximum Ratings	4 4 5 6 7
	1.1 1.2 Acro Logi 3.1 Pin 5.1 5.2 5.3	Acronyms and Abbreviations Logic Data 3.1 Truth Table Pin Configuration Electrical Characteristics

	5.5 5.6	Radiation Resilience	7 7
6	Deta	ailed Description	8
7	7.1	lications Information Applications Example Power Supply Recommendations Application Tips	9 9 10 10
8	Pacl	caging Information	11
9	Orde	ering Information	12
10	Revi	sion History	12
11	Lega	al	13

LIST OF TABLES

1	Truth Table	3
2	Device Pinout	
3	Absolute Maximum Ratings	4
4	Recommended Operating Conditions	5
5	Thermal Information	5

6	DC Electrical Characteristics	6
7	AC Electrical Characteristics	7
8	Radiation Resilience Characteristics	7
9	Ordering Information	12

LIST OF FIGURES

1	AP54RHC301 logic diagram	1
2	Device Pinout	3
3	Load Circuit	7
4	Propagation Delay	7
5		

Output Pin Structure	8
Voter Example	9
Cold Spare Example	
Package Mechanical Drawing	11
Part Number Decoder	12
	Voter ExampleCold Spare ExamplePackage Mechanical Drawing

2 ACRONYMS AND ABBREVIATIONS

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- POR Power On Reset
- RHA Radiation Hardness Assurance
- SEE Single Event Effects
- SEL Single Event Latchup
- SET Single Event Transient
- TID Total Ionizing Dose
- TMR Triple Modular Redundancy
- CDM Charged-device Model
- HBM Human-body Model



3 LOGIC DATA

3.1 TRUTH TABLE

The AP54RHC301 truth table is found in Table 1.H indicates HIGH logic level, L indicates LOW logic level and X indicates DON'T CARE. Subscript **n** reflects one of the two functions in the device (1 to 2).

 Table 1: AP54RHC301 device truth table

	Input		Output			
An	Bn	Cn	Yn	E _{OUT} n		
L	L	L	L	L		
L	L	Н	L	Н		
L	Н	L	L	Н		
L	Н	Н	Н	Н		
Н	L	L	L	Н		
Н	L	Н	Н	Н		
Н	Н	L	Н	Н		
Н	Н	Н	Н	L		

Internal Voting Output Input **E**_{IN} E_{OUT}1 E_{OUT}2 **E**_{DET} L L L L Х Х Н Н Х Н Х Н Х Х Н Н

4 PIN CONFIGURATION

			ì	
A1	1 ()	14	\vdash	Vcc
B1	2	13	\vdash	Edet
C1	3	12	\vdash	Εουτ2
Y1	4	11	\vdash	Y2
Εουτ1	5	10	Þ	C2
Ein	6	9	\vdash	B2
GND	7	8	\vdash	A2

Figure 2: AP54RHC301 device pinout overview

Table 2: AP54RHC301 device pinout description

PIN NAME(S)	PIN NUMBER(S)	DESCRIPTION	
A1, B1, C1	1, 2, 3	Logic Inputs	
A2, B2, C2	8, 9, 10	Logic inputs	
Y1	4	Logic Outputs	
Y2	11		
E _{IN}	6	External Voter Error Input	
E _{OUT} 1	13	Internal Voter Error Outputs	
E _{OUT} 2	12		
E _{DET}	13	Error Detected Output	
V _{CC}	14	Positive Voltage Supply	
GND	7	Ground	



5 ELECTRICAL CHARACTERISTICS

The sign convention for current follows JEDEC standards with negative values representing current sourced from the device and positive values representing current sunk into the device.

5.1 ABSOLUTE MAXIMUM RATINGS

Excursions beyond the values listed in Table 3 may cause permanent damage to the device. Proper function of the device cannot be guaranteed if these values are exceeded, and long-term device reliability may be affected. Functionality of the device at these values, or beyond those listed in Recommended Operating Conditions (Table 4) is not guaranteed.

All parameters are specified across the entire operating temperature range unless otherwise specified.

SYMBOL	PARAMETER		VALUE	UNITS
V _{cc}	Supply Voltage	Supply Voltage		V
VI	Input voltage range		-0.5 to +5.5	V
Vo	Output voltage range		-0.5 to V _{CC} + 0.5 ⁽¹⁾	V
I_{IK} (V ₁ < 0)	Input clamp current		100	mA
I ₀	Continuous output current (per pin)	Continuous output current (per pin)		mA
I _{CC}	Maximum supply current	Maximum supply current		mA
V _{ESD}	ESD Voltago	HBM	4000	V
V ESD	ESD Voltage CDM		500	V
Tj	Operating junction temperature range		-55 to +150	°C
T _{STG}	Storage temperature range		-65 to +150	°C

Table 3: Absolute Maximum Ratings

 $^{(1)}\,$ V_{0} must remain below absolute maximum rating of V_{CC}



5.2 RECOMMENDED OPERATING CONDITIONS

All recommended parameters below are specified across the entire operating temperature range unless otherwise specified.

SYMBOL	PARAMETER		MIN	MAX	UNITS
V _{cc}	Supply voltage		1.65	5.5	V
VI	Input voltage range		0	5.5	V
Vo	Output voltage range		0	V _{CC}	V
	V _{CC} = 1.65	to 1.95 V	1.4	-	
VIH	HIGH-level input voltage	o 2.7 V	1.9	-	V
VIH	$V_{CC} = 3.0 \text{ t}$	0 3.6 V	2.5	-	v
	V _{CC} = 4.5 t	o 5.5 V	3.8	-	
	V _{CC} = 1.65	to 1.95 V	-	0.4	
VIL	LOW-level input voltage	o 2.7 V	-	0.6	V
۷IL	$V_{CC} = 3.0 \text{ t}$	0 3.6 V	-	0.9	v
	V _{CC} = 4.5 t	o 5.5 V	-	1.35	
	V _{CC} = 1.65	to 1.95 V	-	-4	mA
I	HIGH-level output current $V_{CC} = 2.3 \text{ to } 2.7 \text{ V}$ $V_{CC} = 3.0 \text{ to } 3.6 to$	o 2.7 V	-	-8	
I _{ОН}		0 3.6 V	-	-16	
	V _{CC} = 4.5 t	o 5.5 V	-	-24	
	V _{CC} = 1.65	to 1.95 V	-	4	
L.	LOW-level output current	o 2.7 V	-	8	mA
I _{OL}	$V_{CC} = 3.0 \text{ t}$	0 3.6 V	-	16	IIIA
	V _{CC} = 4.5 t	o 5.5 V	-	24	
t _r , t _f	V _{CC} = 1.65	to 1.95 V	-	1000	
	Input rise or fall time V _{CC} = 2.3 t	o 2.7 V	-	600	ns
	(10% - 90%) V _{CC} = 3.0 t	0 3.6 V	-	500	115
	V _{CC} = 4.5 t	o 5.5 V	-	400	

Table 4: Recommended Operating Conditions

Table 5: Thermal Information

SYMBOL	PARAMETER	MIN	TYP	MAX	UNITS
Tj	Operating junction temperature	-55	-	+125	°C
R _{θJA}	Junction to ambient thermal resistance	-	100	-	°C/W



5.3 STATIC CHARACTERISTICS

All parameters are specified across the entire operating temperature range unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	V _{cc}	MIN	ТҮР	MAX	UNITS
	LOW-level output voltage	I ₀ = 100 μΑ	1.65 to 5.5 V	-	0.02	0.05	V
		l _o = 1 mA	1.65 to 5.5 V	-	0.05	0.1	V
		I ₀ = 4 mA	2.3 V	-	0.3	0.6	V
			3.0 V	-	0.2	0.4	V
			4.5 V	-	0.2	0.4	V
			2.3 V	-	0.6	1.0	V
V _{OL}		I ₀ = 8 mA	3.0 V	-	0.4	0.8	V
		_	4.5 V	-	0.3	0.6	V
		I ₀ = 16 mA	3.0 V	-	1.0	1.4	V
			4.5 V	-	1.1	1.5	V
		l ₀ = 24 mA	4.5 V	-	1.1	1.5	V
	HIGH-level output voltage	I ₀ = -100 μA	1.65 to 5.5 V	V _{CC} - 0.1	V _{CC} - 0.02	-	V
		I ₀ = -1 mA	1.65 to 5.5 V	V _{CC} - 0.15	V _{CC} - 0.08	-	V
		I ₀ = -4 mA	2.3 V	1.8	2.0	-	V
			3.0 V	2.6	2.8	-	V
			4.5 V	4.2	4.4	-	V
		I ₀ = -8 mA	2.3 V	1.4	1.7	-	V
V _{OH}			3.0 V	2.2	2.5	-	V
			4.5 V	3.9	4.1	-	V
		I ₀ = -16 mA	3.0 V	1.5	2.0	-	V
			4.5 V	3.3	3.8	-	V
		I ₀ = -24 mA	4.5 V	3.0	3.5	-	V
I _{CC}	Quiescent supply current	V _I = V _{CC} or GND I _O = 0 mA	5.5 V	-	125	205	μA
lı l	Input current	V _I = V _{CC} or GND	1.65 to 5.5 V	-	-	±1	μA
I _{OFF}	Powerdown leakage current ⁽¹⁾	$V_1 = V_{CC} \text{ or } GND$	OFF ⁽²⁾	_	-	5	μA

Table 6: DC Electrical Characteristics

⁽¹⁾ into any input or output port

 $^{(2)}$ V_{cc} is disconnected or at GND potential

AP54RHC301



DATASHEET

5.4 DYNAMIC CHARACTERISTICS

All parameters are specified across the entire operating temperature range unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	V _{cc}	MIN	TYP	MAX	UNITS
t _{pd} ⁽¹⁾	Propagation Delay (Input A_n, B_n or C_n to Output Y_n)		4.5 to 5.5 V	-	7.6	11	ns
		C _L = 50 pF	3.0 to 3.6 V	-	9	13	ns
			2.3 to 2.7 V	-	11	15	ns
			1.65 to 1.95 V	-	17	25	ns
	Dropagation Dolay		4.5 to 5.5 V	-	11	16	ns
+	Propagation Delay (Input A_n, B_n or C_n to Output E_{оит}n)	C _L = 50 pF	3.0 to 3.6 V	-	15	21	ns
t _{err_det}		CL - 30 pr	2.3 to 2.7 V	-	17	24	ns
			1.65 to 1.95 V	-	26	35	ns
			4.5 to 5.5 V	-	7.6	11	ns
+.	t _{pd_err} Propagation Delay (Input E _{IN} to Output E _{DET})	C _L = 50 pF	3.0 to 3.6 V	-	9	13	ns
֊pd_err			2.3 to 2.7 V	-	11	15	ns
			1.65 to 1.95 V	-	17	25	ns
C _{IN}	Input Capacitance ⁽²⁾	$V_{I} = V_{CC} \text{ or } GND$	1.65 to 5.5 V	-	2	4	рF
C _{PD}	Power dissipation	I ₀ = 0 mA	5.5 V		40	-	рĘ
	capacitance ⁽²⁾	f = 1 MHz	5.5 V	_			pF

Table 7: AC Electrical Characteristics

 $^{(1)}$ equivalent to $t_{\text{PLH}}, t_{\text{PHL}}$

⁽²⁾ guaranteed by design

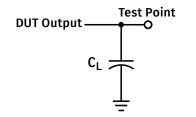
5.5 RADIATION RESILIENCE

For detailed radiation testing reports, please contact Apogee Semiconductor at sales@apogeesemi.com.

Table 8: Radiation Resilience Characteristics

PARAMETER	CONDITIONS	VALUE	UNITS
Total Ionizing Dose (TID)	Please contact Apogee Semiconductor for test report.	30	krad (Si)
SEE LET Threshold	Please contact Apogee Semiconductor for test report.	<80	MeV-cm ² /mg

5.6 CHARACTERISTICS MEASUREMENT INFORMATION



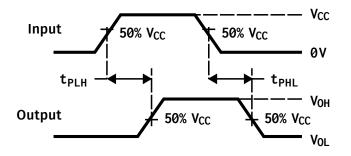


Figure 3: Load circuit for outputs

Figure 4: Propagation delay measurement



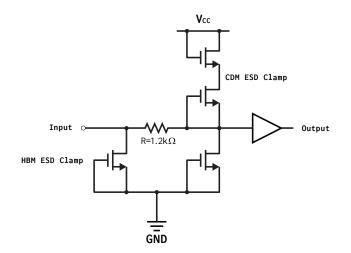
AP54RHC301

6 DETAILED DESCRIPTION

The AP54RHC301 is a dual three-input majority voter gate that that offers two instances of a triple-input voter gate, with individual error outputs, a dedicated "error detected" output, and an external error signal input. Designed to operate from a wide supply voltage of 1.65 to 5.5 V, it has fully redundant input and output stages providing for superior resiliency to single event effects.

The output and input stages are constructed with transient activated clamps (Figure 5, 6) that prevent inadvertent biasing of the V_{CC} power rail through parasitic diodes inherent to conventional input, output, and ESD circuits. The IC also incorporates an internal power-on reset (POR) circuit that prevents the output from driving erroneous results during power-on, and guarantees correct operation at power supply voltages as low as 1.65 V. While the supply is ramping, the POR holds the output buffer in tri-state, a feature that prevents unwanted DC current during cold sparing on input and output pins.

The AP54RHC family's I/O protection circuitry allows for cold sparing configurations as it avoids a leakage current penalty on inputs and outputs while in a power-down state. This can result in considerable power savings in systems where multiple-path redundancy is employed. The ESD clamp circuits for this logic family are designed to support Class 2 ESD levels of 4 kV HBM and 500 V CDM.



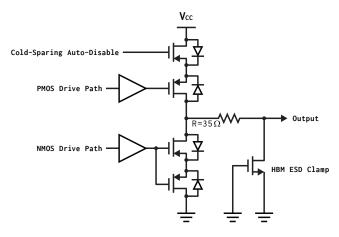


Figure 5: Details of input pin structure

Figure 6: Details of output pin structure

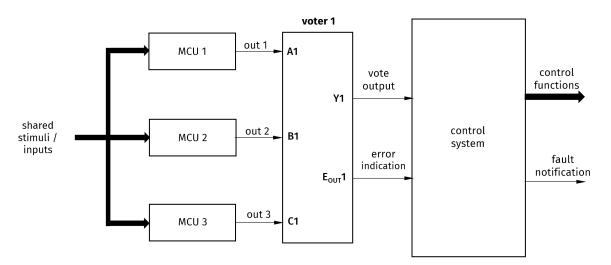


AP54RHC301

7 APPLICATIONS INFORMATION

The voter function of the AP54RHC301 is intended to allow fault-free glitchless operation in logic systems employing triple redundancy, e.g. where specific logic functions are triplicated and all three identical functions are simultaneously active (Figure 7). This may be simple discrete logic that serves a specific purpose, or complex microcontroller-based logic that is responsible for multiple data-processing and control functions.

The three identical blocks are assumed to perform the same operation, share the same stimuli, and produce the same result at a given single-bit output (e.g., an on/off control line that turns on a valve). These three results are compared by the voter to make sure that they are in agreement.





When only two of them are in agreement and the third one is not, the voter's output will produce the result of a majority vote (Y_n), which assumes that a fault has occurred in the single function whose output did not agree with that of the other two. Alongside the vote result, the voter will also produce an error signal (E_{OUT}n), which may be used to produce a fault notification.

This fault may be either the result of permanent damage in that function, or may be the consequence of a SEE, in which case there is a chance that the block will return to normal functionality and the error indication will be reset. The AP54RHC301 contains two instances of this voting function.

7.1 APPLICATIONS EXAMPLE

As the AP54RHC family is radiation-hardened by design and includes internal TMR, it can be utilized in highreliablity applications without additional supporting circuitry or devices. Nonetheless, some application requirements call for fully-redundant designs, where an "A" and a "B" device are required, often on separate power rails.

With the cold-sparing capability of the AP54RHC family, fully redundant "A" and "B" functions may be placed in parallel (as seen in Figure 8) running off redundant power supplies. The inputs and outputs on each one of these functions are assumed to be based on the AP54RHC family, allowing for direct parallel connection without unwanted leakage current paths during cold sparing. In the event of a failure in power supply A or within function A, the system can simply shut power supply A off and switch on power supply B, without requiring additional input or output switching or configuration changes.



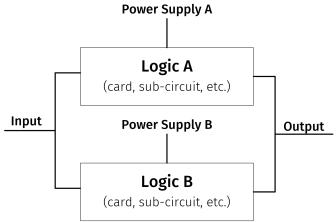


Figure 8: Cold sparing example.

7.2 POWER SUPPLY RECOMMENDATIONS

This device can operate at any voltage within the range specified in Table 4 Recommended Operating Conditions.

At a minimum, a 16 VDC (or higher), X7R-rated 0.1 μF ceramic decoupling capacitor should be placed near (within 1 cm) the V_{cc} pin of the device.

7.3 APPLICATION TIPS

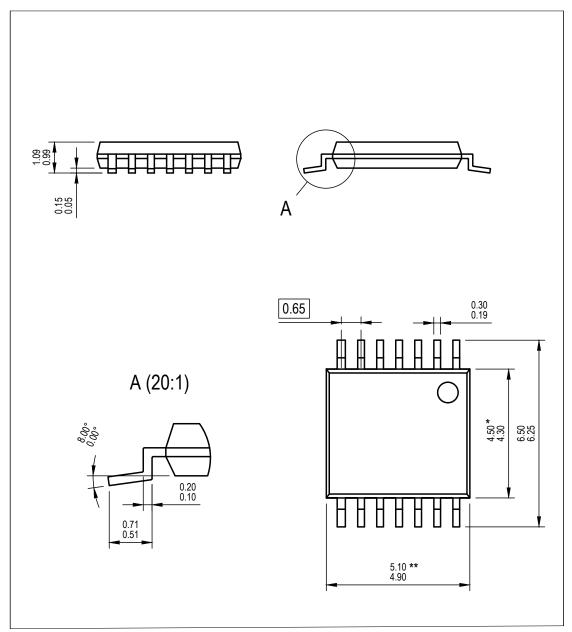
DATASHEET

Unused **inputs** must **not** be left floating. They may be connected to either a low (GND) or high (V_{cc}) bias to provide a known state at the input of the device. Resistors may be used to tie off unused inputs. In the event of a design change, such resistors can be removed, thereby allowing use of the inputs without having to cut traces on the PCB.

An unused **output** may be left floating. It is suggested that it be routed to a test point or similar accessible structure in case the gate needs to be utilized as part of a design revision.



8 PACKAGING INFORMATION



Notes:

1. All linear dimensions are in millimeters. Dimensioning and tolerancing are as per ISO/TS 128-71:2010 2. The part is compliant with JEDEC MO-153 specifications.

* Body width does **not** include interlead flash. Interlead flash shall not exceed 0.25 mm each side. ** Body length does **not** include mold flash, protrusion, or gate burrs. Mold flash, protrusions, and gate burrs shall not exceed 0.15 mm on each side.

Figure 9: Package Mechanical Detail

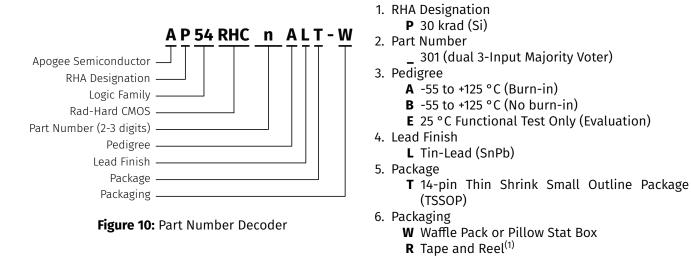


9 ORDERING INFORMATION

Example part numbers for the AP54RHC301 are listed in Table 9. The full list of options for this part can be found in Figure 10. Please contact Apogee Semiconductor sales at sales@apogeesemi.com for further information on sampling, lead time and purchasing on specific part numbers.

Table 9: AP54RHC301 Ordering Information

DEVICE	DESCRIPTION	PACKAGE
AP54RHC301ELT-W	Radiation Hardened Dual 3-Input Majority Voter (for evaluation only)	Plastic TSSOP-14
AP54RHC301ALT-R	Radiation Hardened Dual 3-Input Majority Voter (30 krad (Si))	Plastic TSSOP-14



⁽¹⁾ Contact us for custom reel quantities. Orders less than full reel quantities may be shipped as cut tape.

10 REVISION HISTORY

REVISION	DESCRIPTION	DATE
A06	Updated ordering information.	2021-07-30
A05	Updated dynamic characteristics values.	2021-07-17
A04	Correct pin mappings in logic diagram.	2021-06-17
A03	Revamped static and dynamic characteristics with new test data.	2021-02-24
A02	Update Static and Dynamic characteristics.	2020-10-23
A01	Initial public release.	2020-02-29
A00	Initial internal release.	2019-07-05

For the latest version of this document, please visit https://www.apogeesemi.com.



11 LEGAL

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